

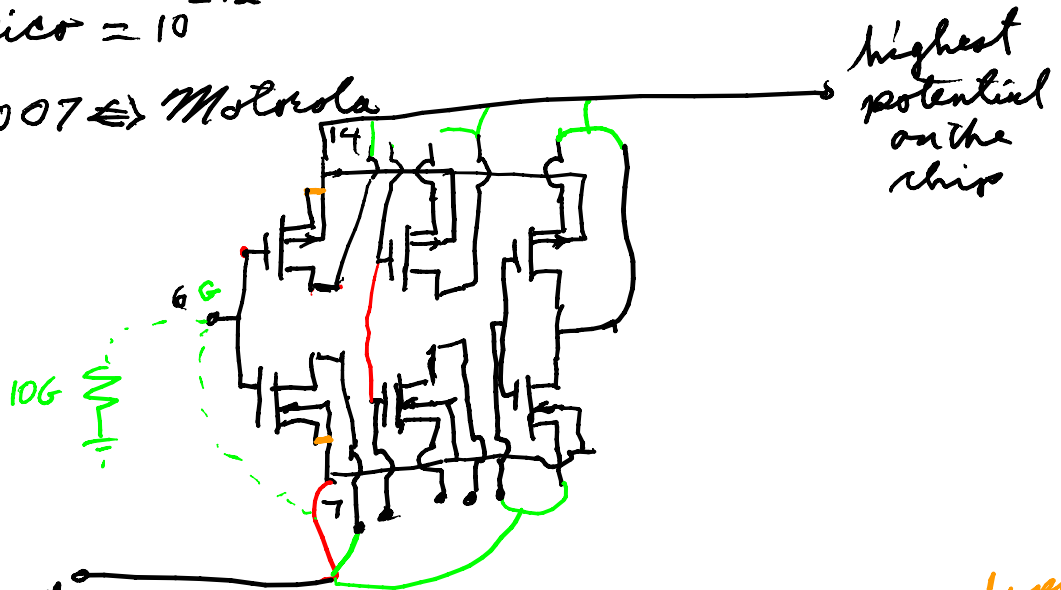
Unit scaling

EE 303 Tu 09/30/08

$m = \text{milli} = 10^{-3}$
 $\mu = \text{micro} = 10^{-6}$
 $k = \text{kilo} = 10^3$
 $\text{MEG} = 10^6$
 $p = \text{pico} = 10^{-12}$

$n = \text{nano} = 10^{-9}$
 $f = \text{femto} = 10^{-15}$
 $G = \text{giga} = 10^9$

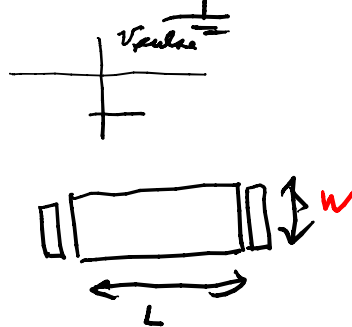
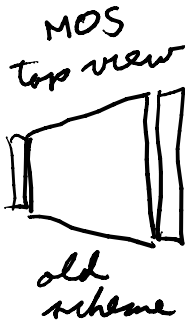
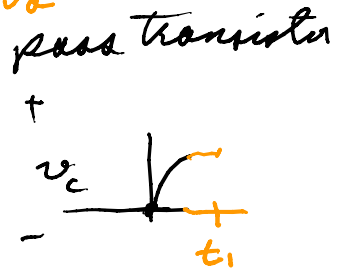
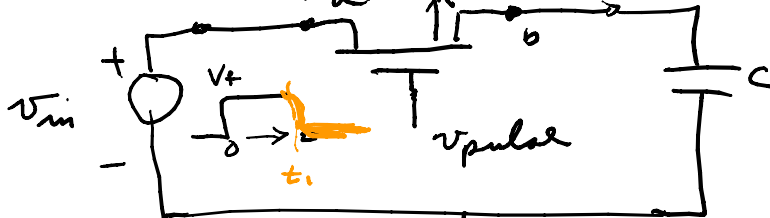
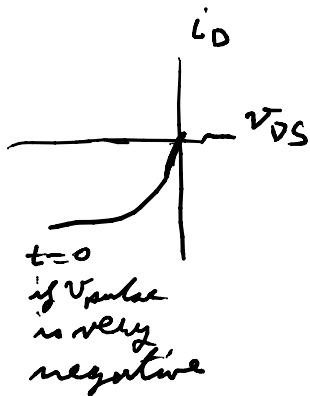
RCA 3600 = 4007 \Rightarrow Motorola

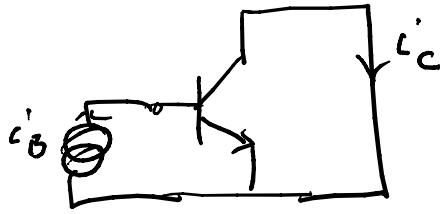


lowest potential on the chip

highest potential on the chip

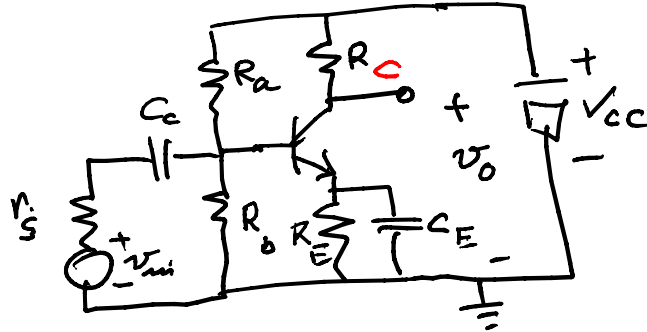
at $t=0+$, $b = \text{drain}$
 i is pass at $t=0+$
 at $t=t_1$, $v_b > v_a \Rightarrow b = S, a = D$
 pass transistor





f_T is the frequency where $\left| \frac{i_c}{i_b}(j\omega) \right| = 1$

Small signal gain



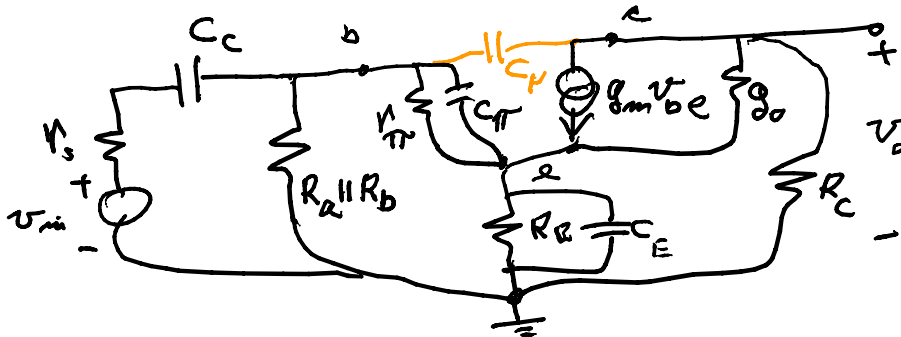
$$r_{\pi} = \frac{1}{g_{\pi}}$$

$g = \text{conductance}$

$$g_m \approx \frac{|I_c|}{V_T}$$

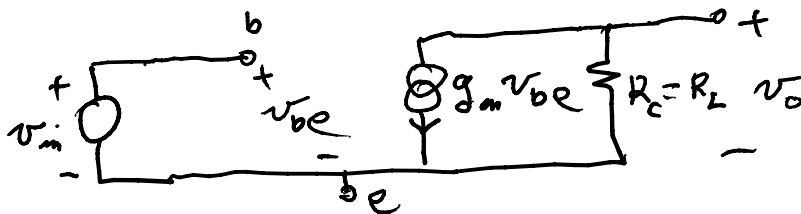
$$g_o = \frac{|I_c|}{V_A}$$

$$g_{\pi} = \frac{g_m}{\beta_0}$$

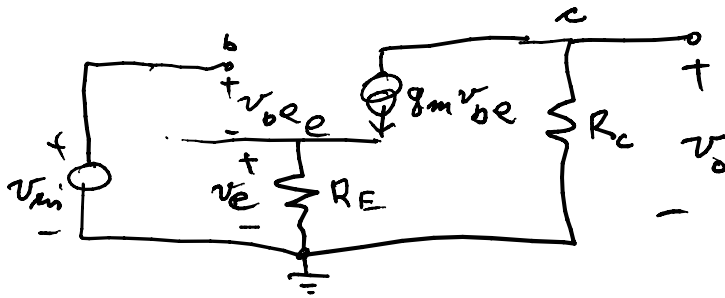


desire $\frac{v_o}{v_{in}}$; $20 \log_{10} \left| \frac{v_o}{v_{in}}(j2\pi f) \right| = \text{Bode plot}$

Key parts $\Rightarrow C_c \rightarrow \text{short}, C_E \rightarrow \text{short}$
 $g_{\pi} \rightarrow 0, C_{\pi} \& C_{\mu} \rightarrow 0, v_s \rightarrow 0; g_o \rightarrow 0$



$$v_o = -(g_m v_{be}) R_L = -g_m R_L v_{in}; G_v = \frac{v_o}{v_{in}} = -g_m R_L$$



$$v_e = R_E \cdot g_m v_{be} ; \quad v_{be} = v_{in} - v_e$$

$$= R_E \cdot g_m (v_{in} - v_e) \rightarrow v_e = \frac{R_E g_m v_{in}}{1 + g_m R_E}$$

$$\text{get } v_{be} = v_{in} - v_e = \left(1 - \frac{R_E g_m}{1 + g_m R_E}\right) v_{in}$$

$$= \frac{1}{1 + g_m R_E} v_{in} = v_{be}$$

$$v_o = -R_C g_m v_{be} = -\frac{R_C g_m}{1 + g_m R_E}$$

with C_E : C_E is in parallel with R_E

$$g_E = \frac{1}{R_E} + s C_E = \frac{1 + s C_E R_E}{R_E} \Rightarrow R_E \Rightarrow \frac{R_E}{1 + s C_E R_E}$$

$$\frac{v_o}{v_{in}} = \frac{-R_C g_m}{1 + g_m \frac{R_E}{1 + s C_E R_E}} = \frac{-R_C g_m (1 + s C_E R_E)}{(1 + g_m R_E) + s C_E R_E}$$